

HIGH-SPEED 3.3V 32K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

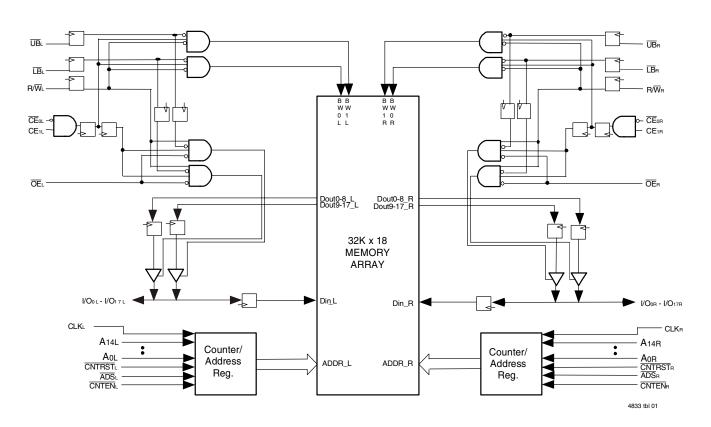
IDT70V3379S

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 4.2/5/6ns (max.)
 - Industrial: 5ns (max)
- Pipelined output mode
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 7.5ns cycle time, 133MHz operation (9.6 Gbps bandwidth)
 - Fast 4.2ns clock to data out
 - 1.8ns setup to clock and 0.7ns hold on all control, data, and address inputs @, 133MHz

- Data input, address, byte enable and control registers
- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±150mV) power supply for core
- LVTTL- compatible, selectable 3.3V (±150mV)/2.5V (±125mV) power supply for I/Os and control signals on each port
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 128-pin Thin Quad Plastic Flatpack (TQFP) and 208-pin fine pitch Ball Grid Array, and 256-pin Ball Grid Array
- Green parts available, see ordering information

Functional Block Diagram



AUGUST 2015

Description:

The IDT70V3379 is a high-speed32Kx18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V3379 has been optimized for applications having unidirectional or bidirectional data flow

in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}0$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode

The 70V3379 can support an operating voltage of either 3.3 V or 2.5 V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3 V.

Pin Configuration^(1,2,3,4)

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
I/O _{9L}	NC	Vss	NC	NC	NC	A 12L	AsL	NC	V _{DD}	CLKL	CNTEN	A 4L	AoL	OPTL	NC	Vss	Α
NC	Vss	NC	Vss	NC	A13L	A9L	NC	CEOL	Vss	ĀDSL	A ₅ L	A ₁ L	Vss	VDDQR	I/O ₈ L	NC	В
V _{DDQ}	I/O _{9R}	VDDQR	V _{DD}	NC	A ₁₄ L	A _{10L}	ŪB∟	CE ₁ L	Vss	R/W̃L	A ₆ L	A 2L	V _{DD}	I/O _{8R}	NC	Vss	С
NC	Vss	I/O _{10L}	NC	NC	A11L	A 7L	ĪΒι	V _{DD}	ŌĒL	ŌNTRS'	Г Аз∟	V _{DD}	NC	VDDQL	I/O7L	I/O7R	D
I/O _{11L}	NC	VDDQR	I/O _{10R}							•			I/O ₆ L	NC	Vss	NC	Е
V _{DDQ}	I/O _{11R}	NC	Vss										Vss	I/O _{6R}	NC	VDDQR	F
NC	Vss	I/O _{12L}	NC										NC	VDDQL	I/O ₅ L	NC	G
V _{DD}	NC	VDDQR	I/O _{12R}					/337					V _{DD}	NC	Vss	I/O _{5R}	Н
V _{DDQ}	V _{DD}	Vss	Vss				ВІ	F-208	3 (5)				Vss	V _{DD}	Vss	VDDQR	J
I/O _{14R}	Vss	I/O13R	Vss					Pin fp p Vie		٨			I/O3R	VDDQL	I/O ₄ R	Vss	K
NC	I/O ₁₄ L	VDDQR	I/O13										NC	I/O ₃ L	Vss	I/O ₄ L	L
VDDQL	NC	I/O _{15R}	Vss										Vss	NC	I/O ₂ R	VDDQR	М
NC	Vss	NC	I/O _{15L}										I/O _{1R}	VDDQL	NC	I/O ₂ L	N
I/O ₁₆	I/O _{16L}	VDDQR	NC	NC	NC	A _{12R}	A ₈ R	NC	V _{DD}	CLK R	CNTEN	A 4R	NC	I/O ₁ L	Vss	NC	Р
Vss	NC	I/O ₁₇	NC	NC	A 13R	A 9R	NC	Œ0R	Vss	ADSR	A _{5R}	A 1R	Vss	VDDQL	I/O _{0R}	VDDQR	R
NC	I/O17L	VDDQL	Vss	NC	A _{14R}	A _{10R}	UB R	CE _{1R}	Vss	R/WR	A ₆ R	A ₂ R	Vss	NC	Vss	NC	Т
Vss	NC	VDD	NC	NC	A _{11R}	A 7R	ŪBR	V _{DD}	ŌĒr	CNTRST	r А зп	Aor	V _{DD}	OPTR	NC	I/Ool	U

4833 drw 02

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 15mm x 15mm x 1.4mm, with 0.8mm ball pitch.
- $5. \;$ This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3,4) (con't.)

70V3379BC BC-256⁽⁵⁾

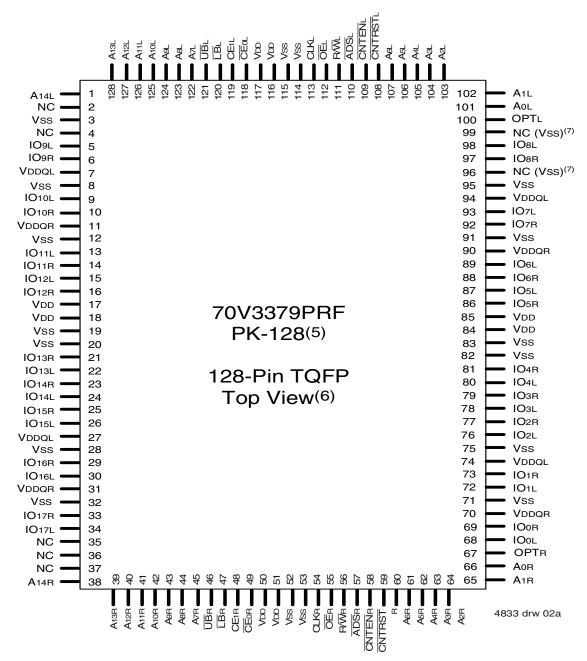
256-Pin BGA Top View⁽⁶⁾

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	NC	NC	NC	A 14L	A 11L	A 8L	NC	CE1L	OEL	CNTENL	A 5L	A 2L	A 0L	NC	NC
B1	B2	B3	B4	B5	B6	B7	B8	B9	B10	B11	B12	B13	B14	B15	B16
NC	NC	NC	NC	NC	A 12L	A 9L	UBL	CE0L	R/WL	CNTRSTL	A 4L	A 1L	VDD	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/O9L	Vss	NC	A 13L	A 10L	A 7L	NC	LBL	CLKL	ADSL	A 6L	A 3L	OPTL	NC	I/O8L
D1	D2	D3	D4	D5	D6	d7	d8	D9	D10	D11	D12	D13	D14	D15	D16
NC	I/O9R	NC	VDD	Vddql	V DDQL	Vddqr	Vddqr	VDDQL	VDDQL	VDDQR	VDDQR	VDD	NC	NC	I/O8R
E1	E2	E3	E4	E5	E6	E7	E8	E9	E10	E11	E12	E13	E14	E15	E16
I/O10R	I/O10L	NC	VDDQL	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	VDD	VDDQR	NC	I/O7L	I/O7R
F1	F2	F3	F4	F5	F6	F7	F8	F9	F10	F11	F12	F13	F14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	VDD	VDDQR	I/O6R	NC	I/O6L
G1	G2	G3	G4	G5	G6	G7	G8	G9	G10	G11	G12	G13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	V SS	Vss	Vss	Vss	Vss	Vss	VDDQL	I/ O 5L	NC	NC
H1	H2	нз	h4	H5	H6	H7	H8	H9	H10	H11	H12	H13	H14	H15	H16
NC	I/O12R	NC	Vddqr	Vss	Vss	V SS	Vss	Vss	Vss	Vss	Vss	VDDQL	NC	NC	I/O5R
J1	J2	J3	J4	J5	J6	J7	J8	^{J9}	J10	J11	J12	J13	J14	J15	J16
I/O13L	I/O14R	I/O13R	V DDQL	Vss	Vss	V SS	Vss	Vss	V SS	Vss	Vss	Vddqr	I/O4R	I/О 3R	I/O4L
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10	K11	K12	K13	K14	K15	К16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	V SS	Vss	Vss	VDDQR	NC	NC	I/ОзL
L1	L2	L3	L4	L5	L6	L7	L8	L9	L10	L11	L12	L13	L14	L15	L16
I/O15L	NC	I/O15R	V DDQR	VDD	Vss	V SS	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2L	NC	I/O2R
M1	M2	мз	m4	M5	M6	M7	M8	M9	M10	M11	M12	M13	M14	M15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	VDD	V SS	Vss	Vss	Vss	VDD	VDD	VDDQL	I/O1R	I/O1L	NC
N1	N2	N3	N4	N5	N6	N7	n8	N9	N10	N11	N12		N14	N15	N16
NC	I/O17R	NC	V DD	VDDQR	V DDQR	Vddql	Vddql	Vddqr	VDDQR	VDDQL	Vddql		NC	I/O0R	NC
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
NC	I/O17L	NC	NC	A 13R	A 10R	A 7R	NC	LBr	CLKR	ADSR	A 6R	A 3R	NC	NC	I/O0L
R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	R13	R14	R15	R16
NC	NC	NC	NC	NC	A 12R	A 9R	UBr	CE0R	R/WR	CNTRSTR	A 4R	A 1R	OPTR	NC	NC
T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11	T12	T13	T14	T15	T16
NC	NC	NC	NC	A 14R	A 11R	A 8R	NC	CE1R	OEr	CNTENR	A 5R	A 2R	A 0R	NC	NC

4833 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3,4) (con't.)



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 14mm x 20mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.
- 7. In the 70V3379 (32K x 18) and 70V3389 (64K x 18), pins 96 and 99 are NC. The upgrade devices 70V3399 (128K x 18) and 70V3319 (256K x 18) assign these pins as Vss. Customers who plan to take advantage of the upgrade path should treat these pins as VSS on the 70V3379 and 70V3389. If no upgrade is needed, the pins can be treated as NC.

Pin Names

Left Port	Right Port	Names
Œ6L, CE1L	CEOR, CE1R	Chip Enables
R/WL	R/W̄R	Read/Write Enable
ŌĒL	OE R	Output Enable
A0L - A14L	A0R - A14R	Address
I/O0L - I/O17L	I/O0R - I/O17R	Data Input/Output
CLKL	CLKr	Clock
ADS L	ĀDS̄R	Address Strobe Enable
CNTENL	<u>CNTEN</u> R	Counter Enable
CNTRSTL	CNTRST _R	Counter Reset
UBL - LBL	UBr - LBr	Byte Enables (9-bit bytes)
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾
OPTL	OPTr	Option for selecting VDDQx ^(1,2)
V	DD	Power (3.3V) ⁽¹⁾
V	SS	Ground (0V)

4833 tbl 01

NOTES

- VDD, OPTx, and VDDQx must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDQX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDQX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Œ	CE ₁	ŪB	ĪΒ	R/W	Upper Byte I/O9-18	Lower Byte I/O ₀₋₈	MODE
Х	↑	L	Н	Н	Н	Х	High-Z	High-Z	All Bytes Deselected
Х	1	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only
Х	1	L	Н	L	Н	L	DIN	High-Z	Write to Upper Byte Only
Х	↑	L	Н	L	L	L	DIN	Din	Write to Both Bytes
L	↑	L	Н	Н	L	Н	High-Z	Dout	Read Lower Byte Only
L	1	L	Н	L	Н	Н	Dоит	High-Z	Read Upper Byte Only
L	1	L	Н	L	L	Н	D оит	Douт	Read Both Bytes
Н	1	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.
- 3. OE is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2)

Address	Previous Address	Addr Used	CLK ⁽⁶⁾	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	1	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0
An	Х	An	1	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	1	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	1	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. Read and write operations are controlled by the appropriate setting of $R\overline{W}$, \overline{CE}_0 , CE_1 , \overline{BE}_0 and \overline{OE}_1 .
- 3. Outputs are in Pipelined mode: the data out will be delayed by one cycle.
- 4. ADS and CNTRST are independent of all other memory control signals including CEo, CE1 and BEn
- 5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE₀, CE₁, BEn.

4833 tbl 04

4833 tbl 06

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	V DD
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTE:

1. This is the parameter TA. This is the "instant on" case tempereature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	50	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	2.375	2.5	2.625	٧
Vss	Ground	0	0	0	٧
VIH	Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7	_	VDDQ + 125mV ⁽²⁾	V
V⊪	Input High Voltage - I/O ⁽³⁾	1.7	_	VDDQ + 125mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.7	٧

4833 tb1 05a

4833 tbl 03

NOTES:

- 1. $V_{IL} \ge -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 125mV.
- To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDQX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	٧
Vss	Ground	0	0	0	٧
V⊪	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0	—	VDDQ + 150mV ⁽²⁾	V
V⊪	Input High Voltage - I/O(3)	2.0	_	VDDQ + 150mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	٧

4833 tbl 05b

- 1. $V_{IL} \ge -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 150mV.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDQX for that port must be supplied as indicated above.

Capacitance⁽¹⁾

$(TA = +25^{\circ}C, F = 1.0MHz) TQFP ONLY$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	8	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF

NOTES:

- 4833 tbl 07
- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V3	379S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
LI	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ	_	10	μΑ
llo	Output Leakage Current	$\overline{\overline{CE}}$ 0 = ViH or CE1 = ViL, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IoL = +4mA, VDDQ = Min.		0.4	٧
Voн (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, VDDQ = Min.	_	0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTES:

- 1. At $VDD \le -2.0V$ input leakages are undefined.
- 2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.4 for details.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ (VDD = 3.3V ± 150mV)

						379S4 I Only	Co	379S5 m'l Ind	70V3379S6 Com'l Only		
Symbol	Parameter	Test Condition	Version		Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	375	460	285	360	245	310	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			285	415			
ISB1	Standby Current	CEL = CER = VIH	COM'L	S	145	190	105	145	95	125	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S			105	175			
ISB2	Standby Current (One Port - TTL	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	265	325	190	260	175	225	mA
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S			190	300	_		
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports CEL and CER ≥ VDDQ - 0.2V,	COM'L	S	6	15	6	15	6	15	mA
	Level Inputs)	$VIN \ge VDDQ - 0.2V \text{ or } VIN \le 0.2V,$ $f = 0^{(2)}$	IND	S			6	30	—		
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$	COM'L	S	265	325	180	260	170	225	mA
	Level Inputs)	$ \begin{array}{ll} \text{VIN} \geq \text{VDDQ} - 0.2 \text{V or VIN} \leq 0.2 \text{V}, \\ \text{Active Port, Outputs Disabled}, \\ \text{f} = \text{fMAX}^{(1)} \\ \end{array} $	IND	S		_	180	300		_	

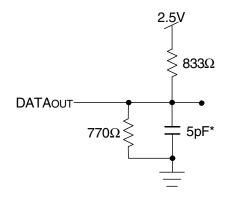
NOTES: 4833 tbl 09

- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CE}x = V_{IL}$ means $\overline{CE}_{0X} = V_{IL}$ and $CE_{1X} = V_{IH}$
 - $\overline{CE}X = VIH \text{ means } \overline{CE}0X = VIH \text{ or } CE1X = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{0x} \leq 0.2 \text{V}$ and $\text{CE1x} \geq \text{V}_{\text{DDQ}}$ 0.2 V
 - $\overline{CEx} \ge V_{DDQ} 0.2V$ means $\overline{CE}_{0x} \ge V_{DDQ} 0.2V$ or $CE_{1x} 0.2V$
 - "X" represents "L" for left port or "R" for right port.

^{1.} At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

AC Test Conditions

out Pulse Levels (Address & Controls) GND to 3.0V/GND to 2.35V			
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.35V		
Input Rise/Fall Times	3ns		
Input Timing Reference Levels	1.5V/1.25V		
Output Reference Levels	1.5V/1.25V		
Output Load	Figures 1, 2, and 3		



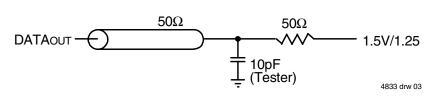


Figure 1. AC Output Test load.

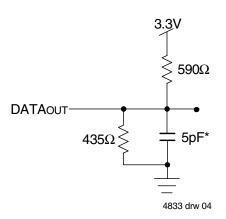


Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz).
*Including scope and jig.

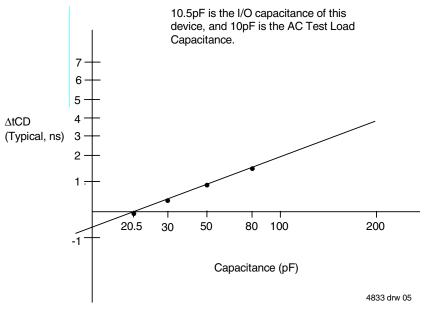


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(1,2)

 $(VDD = 3.3V \pm 150mV, TA = 0°C to +70°C)$

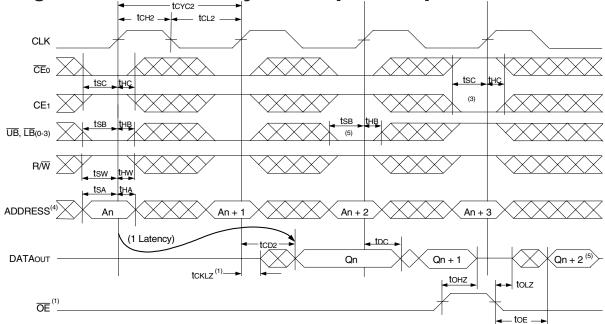
Symbol	Parameter		70V3379S4 Com'l Only		70V3379S5 Com'l & Ind		70V3379S6 Com'l Only	
		Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc2	Clock Cycle Time (Pipelined)	7.5	_	10	_	12	_	ns
tcH2	Clock High Time (Pipelined)	3	_	4		5	_	ns
tal2	Clock Low Time (Pipelined)	3	_	4	_	5	_	ns
tr	Clock Rise Time	_	3	_	3	_	3	ns
tF	Clock Fall Time	_	3	_	3	_	3	ns
tsa	Address Setup Time	1.8		2.0		2.0		ns
tha	Address Hold Time	0.7		0.7		1.0		ns
tsc	Chip Enable Setup Time	1.8		2.0		2.0		ns
thc	Chip Enable Hold Time	0.7		0.7	_	1.0		ns
tsB	Byte Enable Setup Time	1.8		2.0		2.0		ns
tHB	Byte Enable Hold Time	0.7		0.7		1.0		ns
tsw	R/W Setup Time	1.8		2.0		2.0		ns
tHW	R/W Hold Time	0.7		0.7		1.0		ns
tsp	Input Data Setup Time	1.8		2.0		2.0		ns
thD	Input Data Hold Time	0.7	_	0.7	_	1.0	_	ns
tsad	ADS Setup Time	1.8		2.0		2.0		ns
thad	ADS Hold Time	0.7		0.7	_	1.0		ns
tscn	CNTEN Setup Time	1.8		2.0	_	2.0		ns
thon	CNTEN Hold Time	0.7	_	0.7	_	1.0	_	ns
tsrst	CNTRST Setup Time	1.8		2.0		2.0		ns
thrst	CNTRST Hold Time	0.7		0.7		1.0		ns
tOE ⁽¹⁾	Output Enable to Data Valid	_	4	_	5	_	6	ns
toLz	Output Enable to Output Low-Z	0		0	_	0		ns
tонz	Output Enable to Output High-Z	1	4	1	4.5	1	5	ns
tCD2	Clock to Data Valid (Pipelined)	_	4.2	—	5		6	ns
toc	Data Output Hold After Clock High	1		1		1	_	ns
tckHz	Clock High to Output High-Z	1	3	1	4.5	1.5	6	ns
tcklz	Clock High to Output Low-Z	1	_	1	—	1	_	ns
Port-to-Port I	Delay	•	-	-	-	-	-	-
tco	Clock-to-Clock Offset	6	_	8		10	_	ns

NOTES:

^{1.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}) .

^{2.} These values are valid for either level of VDDQ (3.3V/2.5V). See page 4 for details on selecting the desired I/O voltage levels for each port.

Timing Waveform of Read Cycle for Pipelined Operation⁽²⁾

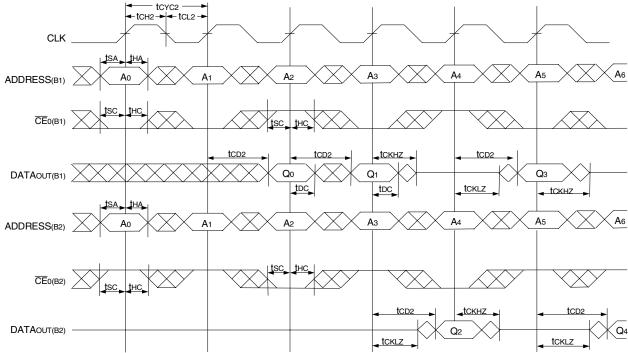


NOTES:

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- 1. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge. 2. $\overline{\text{ADS}} = \text{VIL}$, $\overline{\text{CNTEN}}$ and $\overline{\text{CNTRST}} = \text{VIH}$.
- 3. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\overline{\text{CE}}_1 = \text{V}_{\text{IL}}$, $\overline{\text{UB}}$, $\overline{\text{LB}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If $\overline{\mathsf{UB}}$ or $\overline{\mathsf{LB}}$ was HIGH, then the appropriate Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).

Timing Waveform of a Multi-Device Pipelined Read^(1,2)

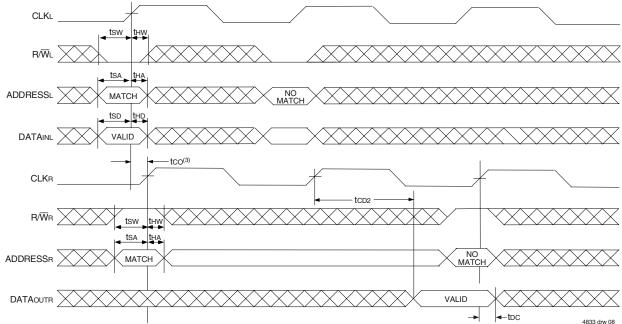


NOTES:

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- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V3379 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{UB}}$, $\overline{\text{LB}}$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; CE1(B1), CE1(B2), R/W, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.

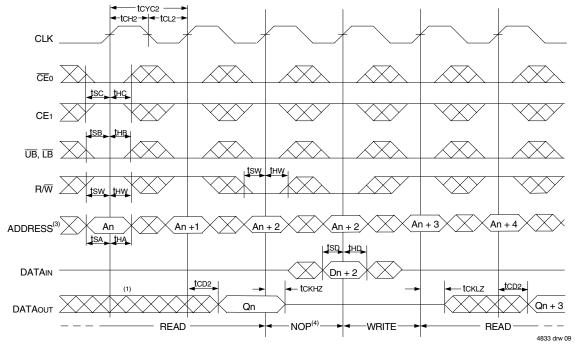
Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2)



NOTES:

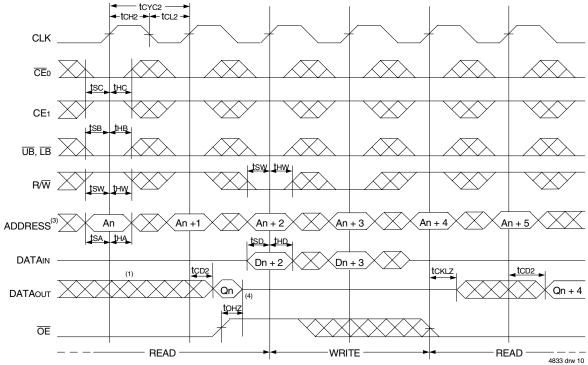
- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 2. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 3. If tco ≤ minimum specified, then data from right port read is not valid until following right port clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from right port read is available on first right port clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc + tcp2).

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)⁽²⁾



- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL, \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 3. Addresses do not have to be accessed sequentially since \overline{ADS} = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

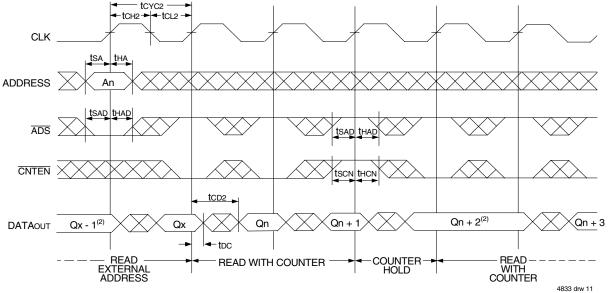
Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(2)



NOTES:

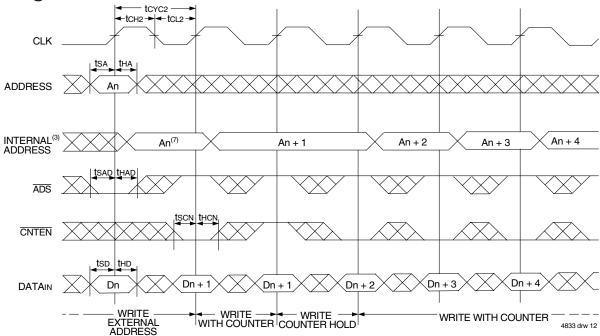
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; $\overline{CE_1}$, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

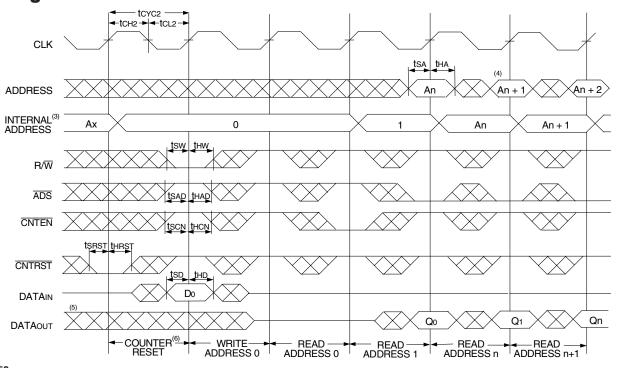


- 1. $\overline{CE_0}$, \overline{OE} , \overline{UB} , \overline{LB} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance⁽¹⁾



Timing Waveform of Counter Reset⁽²⁾



NOTES:

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- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle: ADDR 0 will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

Functional Description

The IDT70V3379 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counterenable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on CE0 or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V3379s for depth expansion configurations. Two cycles are required with $\overline{\text{CE}}_0$ LOW and CE1 HIGH to re-activate the outputs.

Depth and Width Expansion

The IDT70V3379 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V3379 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.

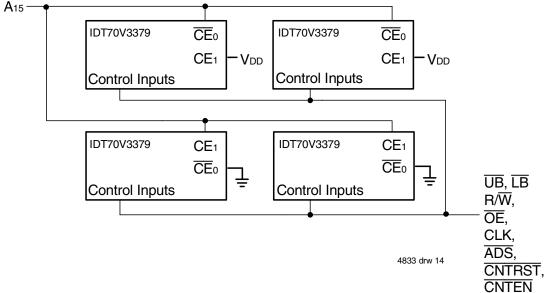
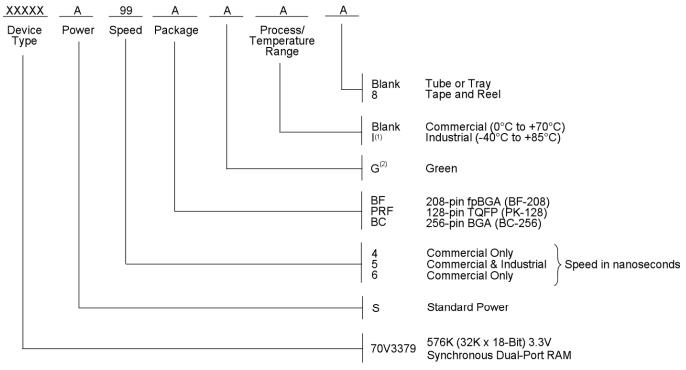


Figure 4. Depth and Width Expansion with IDT70V3379

Ordering Information



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NOTES:

- 1. Contact your local sales office for Industrial temp range in other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

01/18/98:	Initial Public Release				
03/15/99:	Page 10 Additional Notes				
04/28/99:	Added fpBGA package				
06/08/99:	Page 2 Changed package body height from 1.5mm to 1.4mm				
06/11/99:	Page 5 Deleted note 6 for Table II				
07/14/99:	Page 2 Corrected pin to T3 to VDDQL				
08/04/99:	Page 6 Improved power numbers				
10/04/99:	Upgraded speed to 133MHz, added 2.5V I/O capability				
11/12/99:	Replaced IDT logo				
02/28/00:	Added new BGA package, added full 2.5V interface capability				
05/01/00:	Page 2 Added ball pitch				
	Page 3 Renamed pins				
	Page 6 Made corrections to Truth Table				
	Page 9 Changed Ω numbers in figure 2				
06/07/00:	Page 4 Added information to pin and pin notes				
	Page 6 Increased storage temperature parameter				
	Clarified TA Parameter				
	Page 8 DC Electrical parameters—changed wording from "open" to "disabled"				
	Removed note 7 on DC Electrical Characteristics table				

Datasheet Document History (con't)

01/10/01: Page 1 Changed 64K to 32K in block drawing

Removed Preliminary status

04/10/01: Added Industrial Temperature Ranges and removed related notes

12/12/01: Page 2, Added date revision to pin configurations

3&4

Page 6 Removed industrial temp footnote from table 04

Page 8 Removed industrial temp for 6ns from DC & AC Electrical Characteristics

& 10

Page 16 Removed industrial temp from 6ns in ordering information

Added industrial temp footnote

Page 1 Replaced ™ logo with ® logo

& 17

01/05/06: Page 1 Added green availability to features

Page 16 Added green indicator to Ordering Information

02/08/06: Page 5 Changed footnote 2 for Truth Table I from ADS, CNTEN, CNTRST = VIH to ADS, CNTEN, CNTRST = X

07/25/08: Page 8 Corrected a typo in the DC Chars table 01/19/09: Page 16 Removed "IDT" from orderable part number

08/11/15: Page 2 & 3 Removed date from all of the pin configurations 206-pin fpBGA, 128-pin TQFP & 256-pin PGA respectively

Page 16 Added Tape & Reel to Ordering Information

